

N-Ch 100V Fast Switching MOSFETs

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

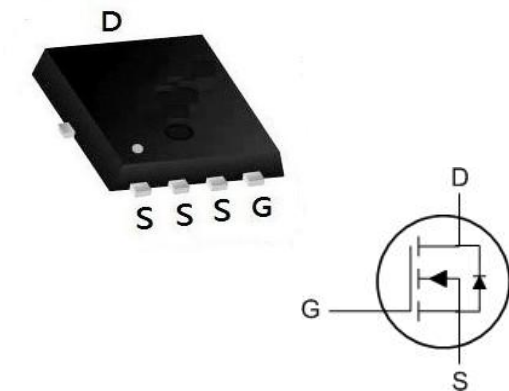


BVDSS	RDSON	ID
100V	10mΩ	40A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	40	A
	$T_C = 100^\circ\text{C}$		18.5	
Pulsed Drain Current ¹		I_{DM}	120	A
Single Pulse Avalanche Energy ²		EAS	80	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	67.5	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	45	$^\circ\text{C/W}$
Thermal Resistance from Junction-to-Lead	$R_{\theta JC}$	1.85	$^\circ\text{C/W}$

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V
Gate-Body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	2.5	V
Drain-Source on-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	10	12.5	mΩ
			V _{GS} = 4.5V, I _D = 10A	-	12	16	
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 20A	-	54	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 50V, V _{GS} =0V, f =1MHz	-	1208	-	pF
Output Capacitance		C _{oss}		-	144	-	
Reverse Transfer Capacitance		C _{rss}		-	11.3	-	
Gate Resistance		R _G	f =1MHz	-	1.8	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DS} = 50V, I _D = 20A	-	22.7	-	nC
Gate-Source Charge		Q _{gs}		-	3	-	
Gate-Drain Charge		Q _{gd}		-	5	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} = 50V, R _G = 3Ω, I _D = 20A	-	9.2	-	ns
Rise Time		t _r		-	3.6	-	
Turn-off Delay Time		t _{d(off)}		-	25.6	-	
Fall Time		t _f		-	4.4	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F = 20A, dI/dt = 100A/μs	-	30	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	42	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	40	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.4mH, I_{AS}=20A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Characteristics

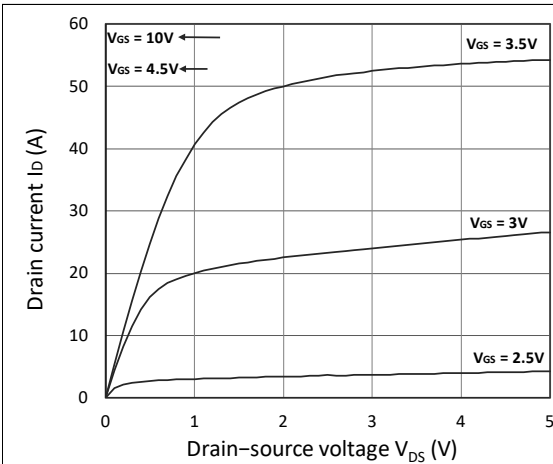


Figure 1. Output Characteristics

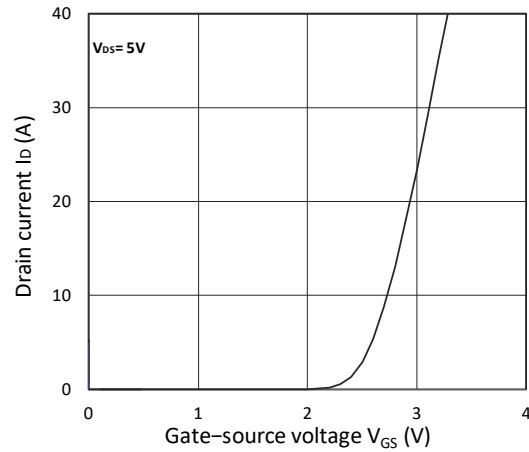


Figure 2. Transfer Characteristics

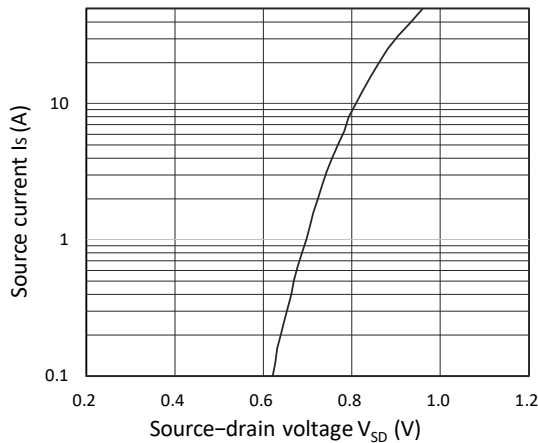


Figure 3. Forward Characteristics of Reverse

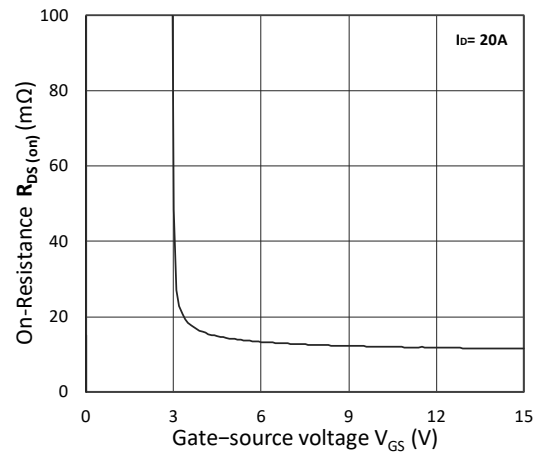


Figure 4. $R_{DS(on)}$ vs. V_{GS}

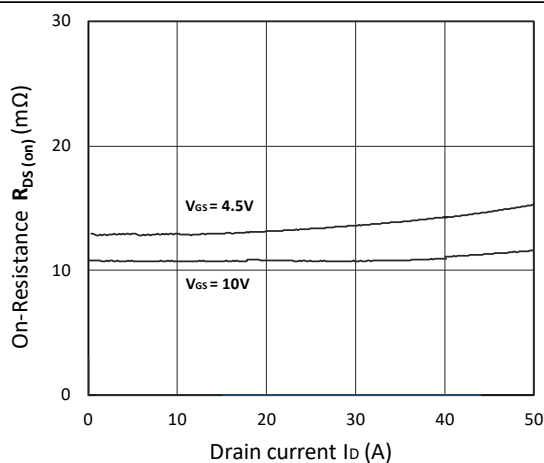


Figure 5. $R_{DS(on)}$ vs. I_D

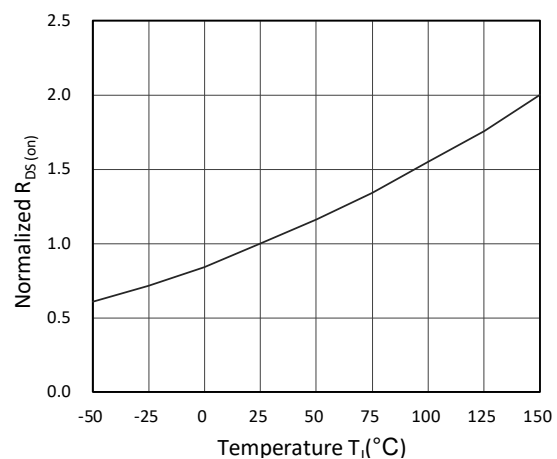


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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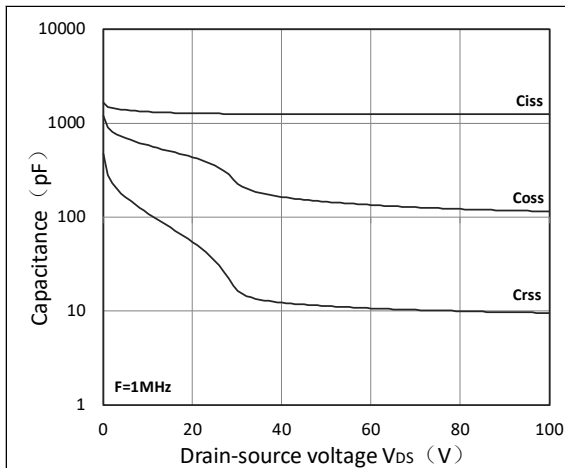


Figure 7. Capacitance Characteristics

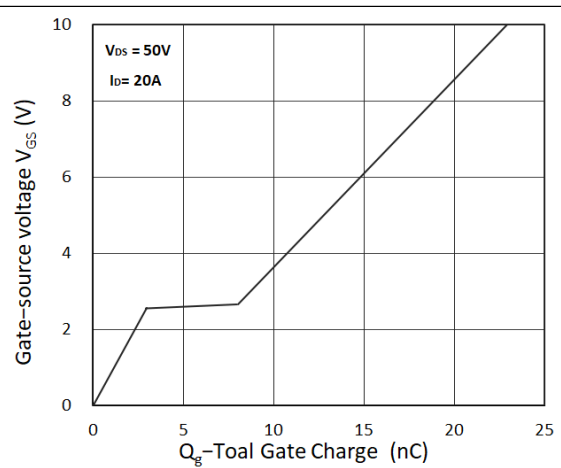


Figure 8. Gate Charge Characteristics

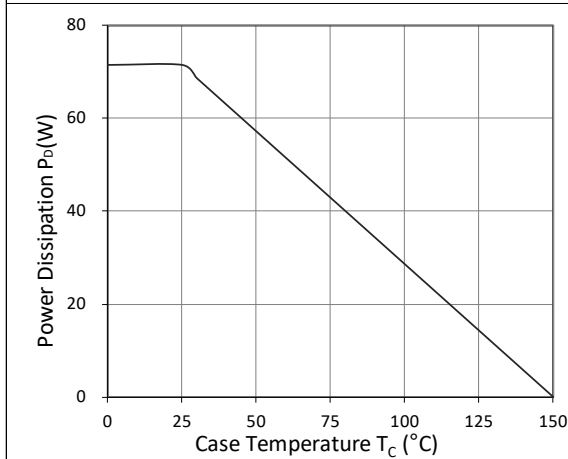


Figure 9. Power Dissipation

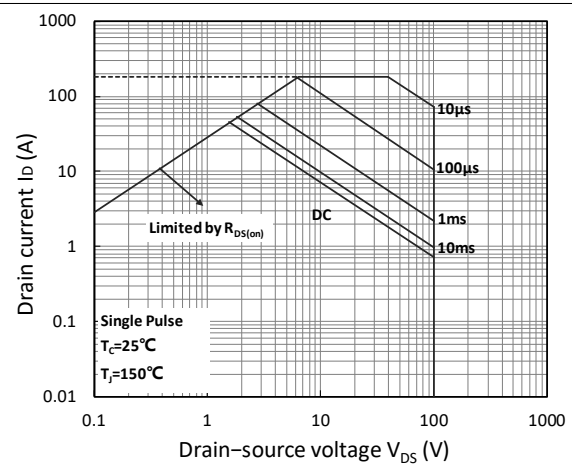


Figure 10. Safe Operating Area

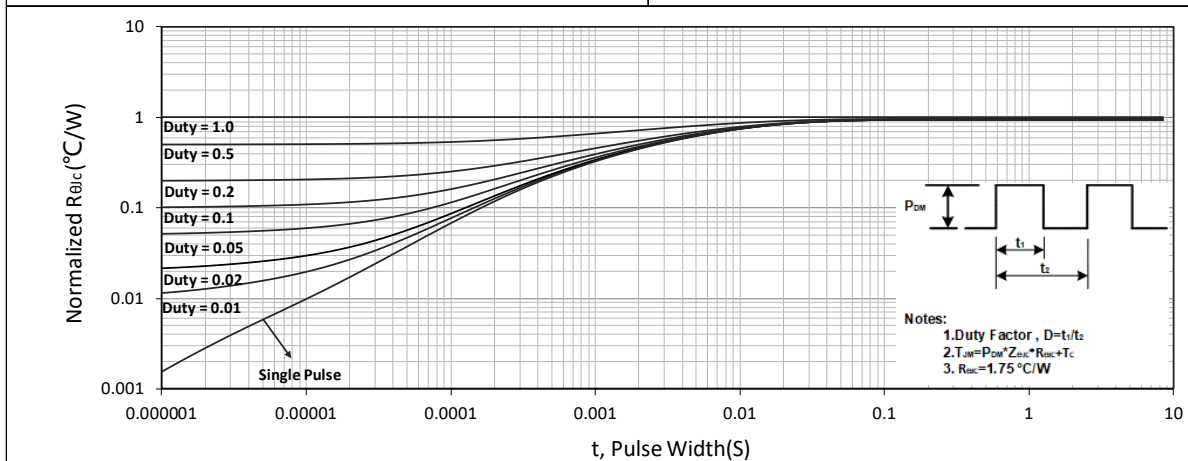


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

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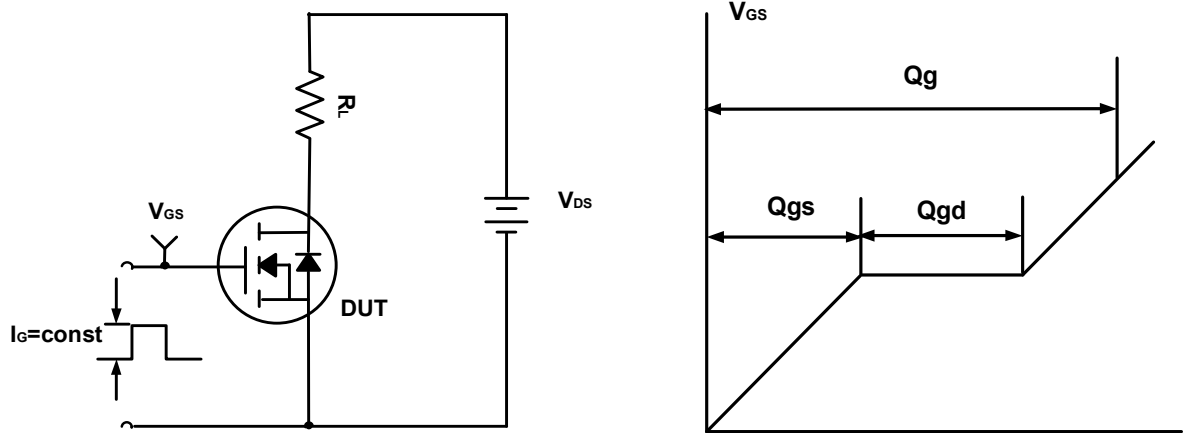


Figure A. Gate Charge Test Circuit & Waveforms

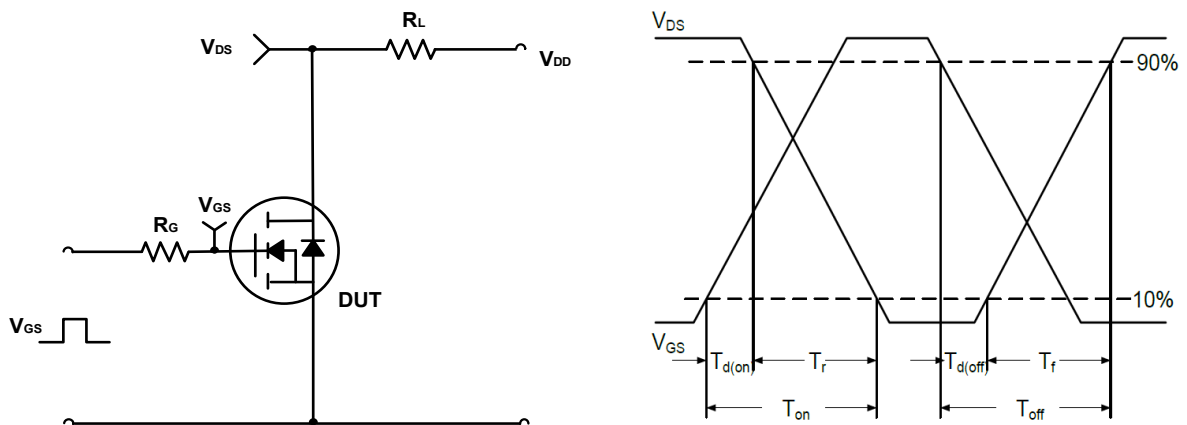


Figure B. Switching Test Circuit & Waveforms

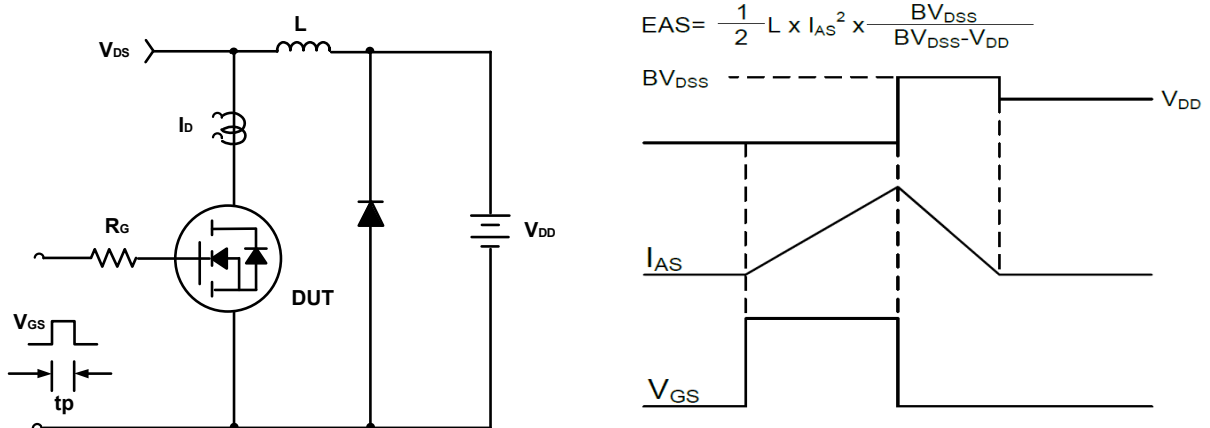
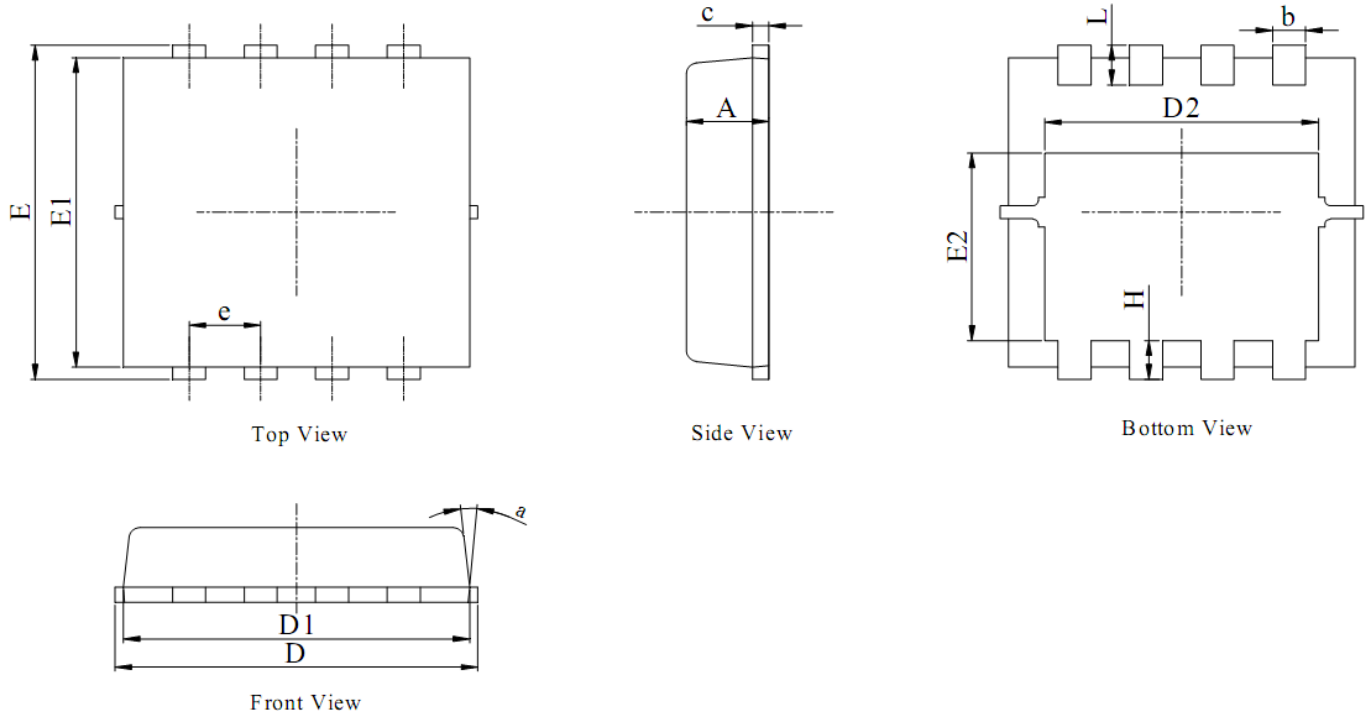


Figure C. Unclamped Inductive Switching Circuit & Waveforms

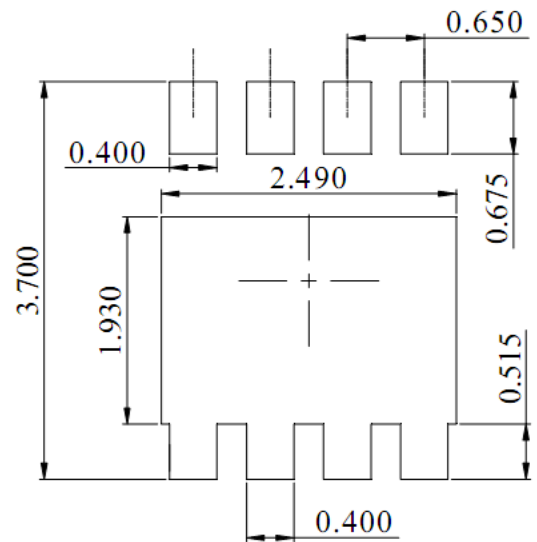
Package Mechanical Data-PDFN3333-8L-Single



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS